

1. ~~41.~~ (Amended) A transistor structure, comprising:

a gate oxide layer over a semiconductive substrate, the gate oxide layer comprising silicon dioxide and having a thickness of about 5Å; the gate oxide layer having a nitrogen-enriched region which is only in an upper half of the gate oxide layer;

at least one conductive layer over the gate oxide layer; and

source/drain regions within the semiconductive substrate; the source/drain regions being gatedly connected to one another by the conductive layer.

2. ~~42.~~ The structure of claim ~~41~~<sup>1</sup> wherein the conductive layer comprises conductively-doped silicon.

3. ~~43.~~ The structure of claim ~~41~~<sup>1</sup> wherein the conductive layer comprises p-type conductively-doped silicon.